

YJ Planar Schottky Barrier Diode Die Specification

30V 0.2A,13mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB013L030AG-155E

Main Products Characteristics

- Average forward current: $I_F(AV) = 0.2 \text{ A}$
- Maximum operating junction temperature: $T_j = 125 \text{ }^\circ\text{C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: AL/3.915um

Maximum Ratings

Static Electrical Characteristics ($T_a = 25^\circ\text{C}$)

$I_F = 200\text{mA}$

Pulse Test: $t_p = 800 \mu\text{s}$, 2%

Device Schematics and Outline Drawing

Die Thickness *

Die Size **

Top Metal Pad

Active Area

Top Metal

Back Metal

Steet width

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Recommended Storage Environment:

does not guarantee device performance after assembly.

Store in original container, in dessicated nitrogen, with no contamination.

All operating parameters must be valida14(i)14(d)9(a)9(14)da 4(d)9(a)a [R](i)14(t)-4[R] muarater apificatiomaRmuarates